In the Specification:

Please replace the paragraph beginning on page 2, line 2 with the following rewritten paragraph:

In a high-density magnetic disk of the future, a recording density of 40 Gbit/inch^2 is projected. In such a high-density magnetic recording device, the magnetic disk carries recording tracks with a pitch of 57 - 80 kTPI, which corresponds to a track separation of 0.45 - 0.32μm. In order to ~~pickup~~ pick up magnetic signals from such high-density tracks, it is necessary to narrow the width (read-core width) of the giant magneto-resistive sensor to be 0.25μm or less. In order to reduce the width of the giant magneto-resistive magnetic sensor, it is inevitable to apply a photolithographic process.

Please replace the paragraph beginning on page 4, line 3 with the following rewritten paragraph:

In the construction of FIG.1, it will be noted that there ~~is~~ are formed regions 16A and 16B in the magneto-resistive layer 13, more precisely in the free layer of the magneto-resistive layer 13, in which the direction of magnetization does not change in response to the external magnetic field Hsig, along the boundary to the domain-control region 12A or 12B. It should be noted that the magnetization 15 of the domain-control region 12A or 12B causes a pinning of magnetization in the free layer in correspondence to the foregoing regions 16A and 16B. Thus, the foregoing regions 16A and 16B form a dead zone. In view of

B2 the fact that the sensing current 14 flows through such dead zones 16A and 16B, the signal-to-noise ratio of the sensing current 14, and hence the sensitivity of the spin-valve magnetic sensor 10 of FIG.1, is inevitably deteriorated. This problem becomes particularly conspicuous when the magneto-resistive region 13 has a reduced width W.

Please replace the paragraph beginning on page 10, line 20 with the following rewritten paragraph:

B3 Next, in the step of FIG.3C, a ferromagnetic layer of CoCrPt is deposited at both lateral ~~sizes~~ sides of the patterned spin-valve structure 100 by a sputtering process while using the resist pattern 130 as a mask, and domain control regions 115A and 115B of CoCrPt are formed in correspondence to the domain control regions 12A and 12B of FIG.2. It should be noted that FIG.3C shows the state in which the resist pattern 130 is removed by an ashing process after the formation of the domain control regions 115A and 115B.